

ABSTRACT OF THE DISCLOSURE

A semiconductor device having high reliability, in which TFTs with appropriate structures for the circuit functions are arranged, is provided. Gate insulating films (115) and (116) of a driver TFT are designed thinner than a gate insulating film (117) of a pixel TFT in a semiconductor device having a driver circuit and a pixel section on the same substrate. In addition, the gate insulating films (115) and (116) of the driver TFT and a dielectric (118) of a storage capacitor are formed at the same time, so that the dielectric (118) may be extremely thin, and a large capacity can be secured.

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